

TO-92 Plastic-Encapsulate Transistors

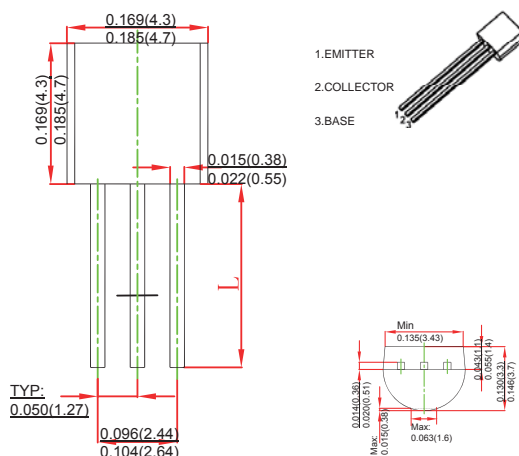
FEATURE

- Excellent h_{FE} linearity
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any

TO-92



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-500	mA
P _C	Collector Dissipation	625	mW
T _J	Junction Temperature	150	°C
T _{stg}	Junction and Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS Ta =25 °C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CB0}	I _C = -100uA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, I _B =0	-25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100uA, I _C =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} = -40V, I _E =0			-0.1	uA
Collector cut-off current	I _{CEO}	V _{CE} = -20V, I _B =0			-0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = - 3V, I _C =0			-0.1	uA
DC current gain	h _{FE(1)}	V _{CE} = -1V, I _C = -50mA	85		400	
	h _{FE(2)}	V _{CE} = -1V, I _C = -500mA	50			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA, I _B =-50mA			-0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-500mA, I _B =-50mA			-1.2	V
Transition frequency	f _T	V _{CE} =- 6V, I _C =-20mA f =30MHz	150			MHZ

CLASSIFICATION OF h_{FE(1)}

Rank	B	C	D	D3
Range	85-160	120-200	160-300	300-400

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

